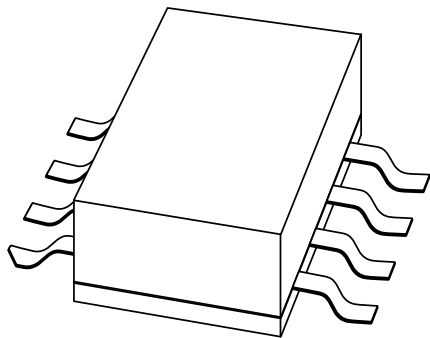


DISCRETE SEMICONDUCTORS

DATA SHEET



BLF404 UHF power MOS transistor

Product specification
Supersedes data of 1998 Jan 29

2003 Sep 26

UHF power MOS transistor

BLF404

FEATURES

- High power gain
- Easy power control
- Gold metallization
- Good thermal stability
- Withstands full load mismatch
- Designed for broadband operation.

APPLICATIONS

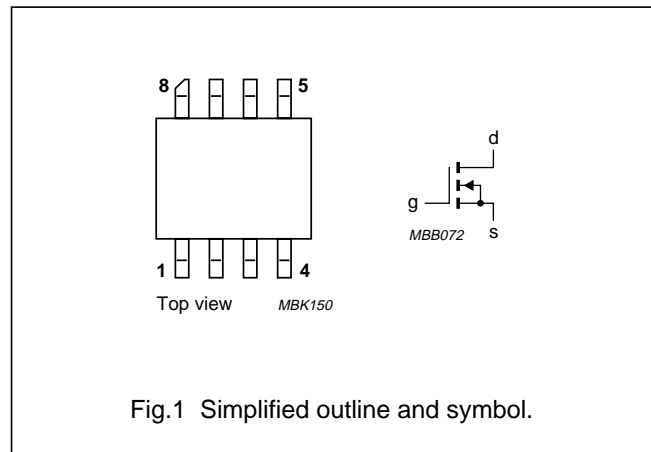
- Communication transmitters in the VHF/UHF range with a nominal supply voltage of 12.5 V.

DESCRIPTION

Silicon N-channel enhancement mode vertical D-MOS power transistor in an 8-lead SOT409A SMD package with a ceramic cap.

PINNING - SOT409A

PIN	DESCRIPTION
1, 8	source
2, 3	gate
4, 5	source
6, 7	drain



QUICK REFERENCE DATA

RF performance at $T_{mb} \leq 60^\circ\text{C}$ in a common source test circuit.

MODE OF OPERATION	f (MHz)	V_{DS} (V)	P_L (W)	G_p (dB)	η_D (%)
CW class-AB	500	12.5	4	≥ 10	≥ 50

CAUTION

This product is supplied in anti-static packing to prevent damage caused by electrostatic discharge during transport and handling. For further information, refer to Philips specs.: SNW-EQ-608, SNW-FQ-302A, and SNW-FQ-302B.

UHF power MOS transistor

BLF404

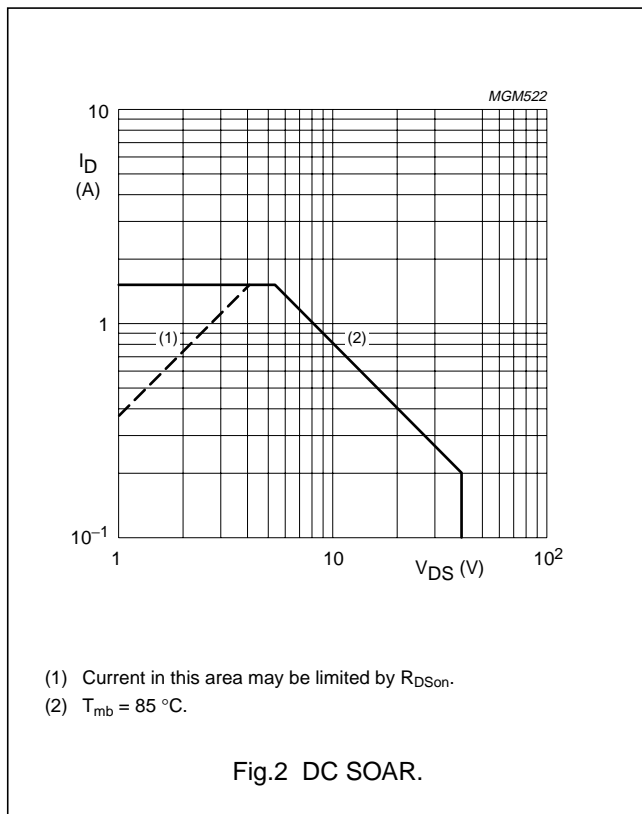
LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{DS}	drain-source voltage		-	40	V
V_{GS}	gate-source voltage		-	± 20	V
I_D	drain current (DC)		-	1.5	A
P_{tot}	total power dissipation	$T_{mb} \leq 85\text{ }^\circ\text{C}$	-	8.3	W
T_{stg}	storage temperature		-65	+150	$^\circ\text{C}$
T_j	junction temperature		-	200	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-mb}$	thermal resistance from junction to mounting base	$T_{mb} \leq 85\text{ }^\circ\text{C}, P_{tot} = 8.3\text{ W}$	12.1	K/W



UHF power MOS transistor

BLF404

CHARACTERISTICS

 $T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified.

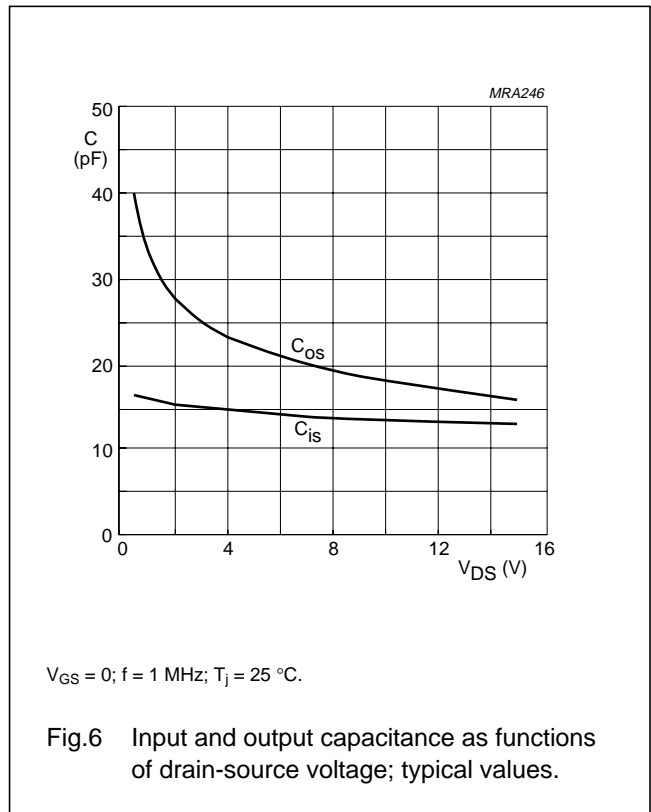
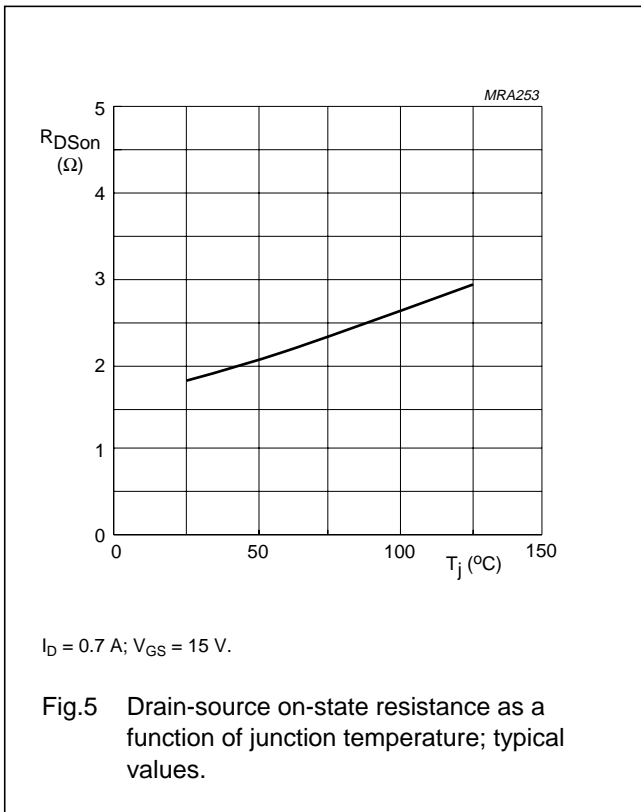
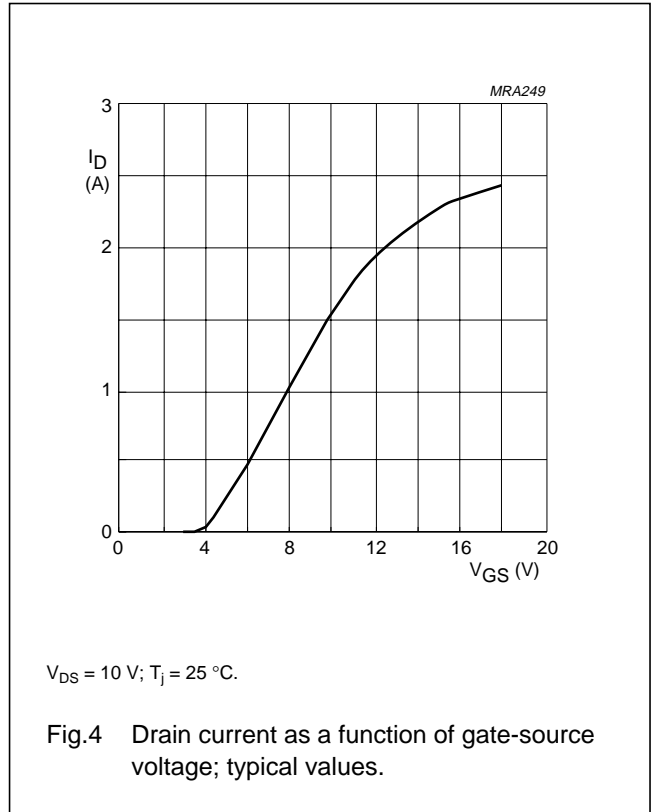
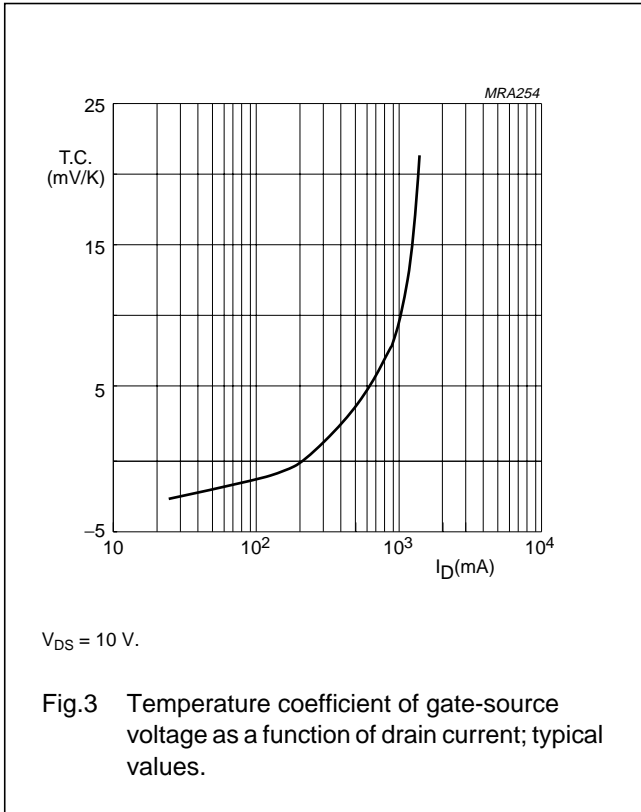
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0; I_D = 5\text{ mA}$	40	–	–	V
V_{GSth}	gate-source threshold voltage	$I_D = 50\text{ mA}; V_{DS} = 10\text{ V}$	2	–	4.5	V
I_{DSS}	drain-source leakage current	$V_{GS} = 0; V_{DS} = 12.5\text{ V}$	–	–	0.5	mA
I_{GSS}	gate-source leakage current	$V_{GS} = \pm 20\text{ V}; V_{DS} = 0$	–	–	1	μA
I_{DSX}	on-state drain current	$V_{GS} = 15\text{ V}; V_{DS} = 10\text{ V}$	–	2.3	–	A
R_{DSon}	drain-source on-state resistance	$I_D = 0.7\text{ A}; V_{GS} = 15\text{ V}$	–	1.8	2.7	Ω
g_{fs}	forward transconductance	$I_D = 0.7\text{ A}; V_{DS} = 10\text{ V}$	200	270	–	mS
C_{is}	input capacitance	$V_{GS} = 0; V_{DS} = 12.5\text{ V}; f = 1\text{ MHz}$	–	14	–	pF
C_{os}	output capacitance	$V_{GS} = 0; V_{DS} = 12.5\text{ V}; f = 1\text{ MHz}$	–	17	–	pF
C_{rs}	feedback capacitance	$V_{GS} = 0; V_{DS} = 12.5\text{ V}; f = 1\text{ MHz}$	–	3	–	pF

 V_{GS} group indicator

GROUP	LIMITS (V)		GROUP	LIMITS (V)	
	MIN.	MAX.		MIN.	MAX.
A	2.0	2.1	O	3.3	3.4
B	2.1	2.2	P	3.4	3.5
C	2.2	2.3	Q	3.5	3.6
D	2.3	2.4	R	3.6	3.7
E	2.4	2.5	S	3.7	3.8
F	2.5	2.6	T	3.8	3.9
G	2.6	2.7	U	3.9	4.0
H	2.7	2.8	V	4.0	4.1
J	2.8	2.9	W	4.1	4.2
K	2.9	3.0	X	4.2	4.3
L	3.0	3.1	Y	4.3	4.4
M	3.1	3.2	Z	4.4	4.5
N	3.2	3.3			

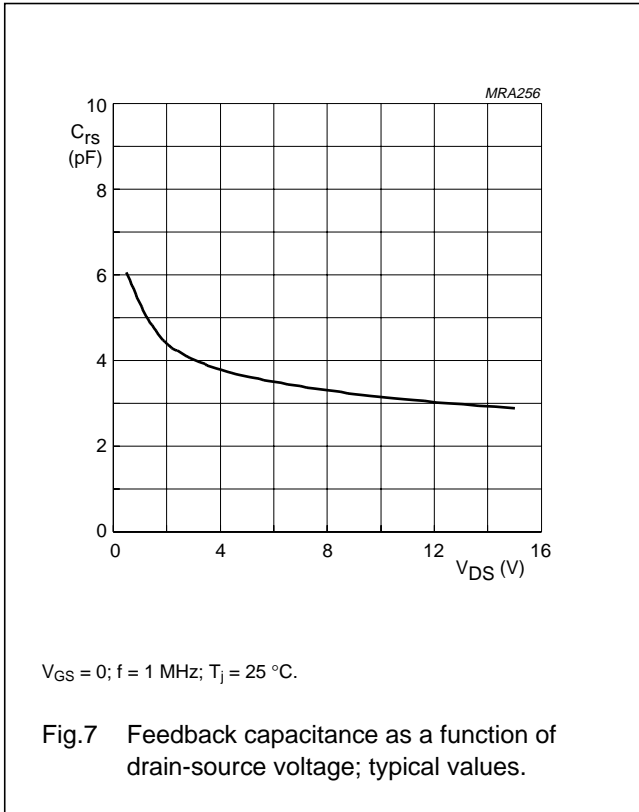
UHF power MOS transistor

BLF404



UHF power MOS transistor

BLF404



APPLICATION INFORMATION

RF performance at $T_{mb} \leq 60$ °C in a common source test circuit with the device soldered on a printed-circuit board with through metallized holes.

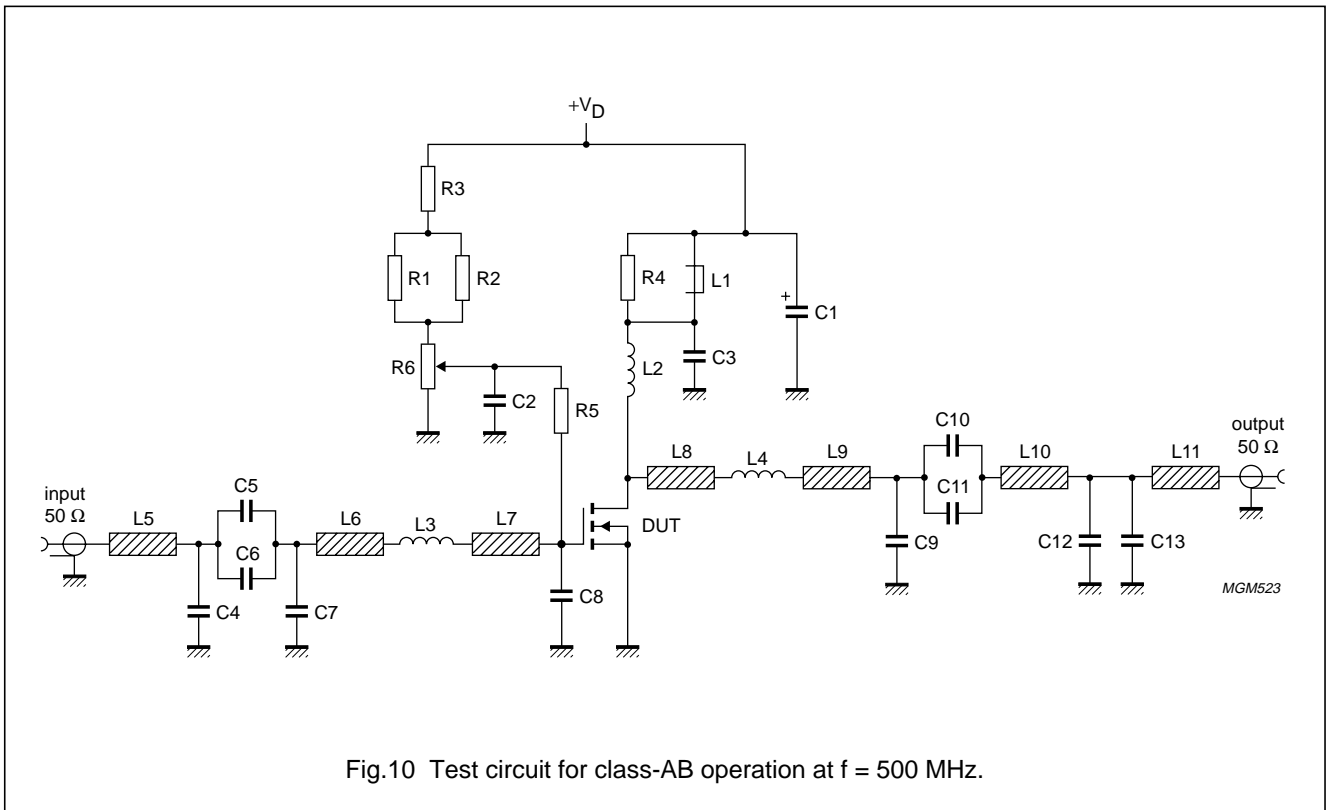
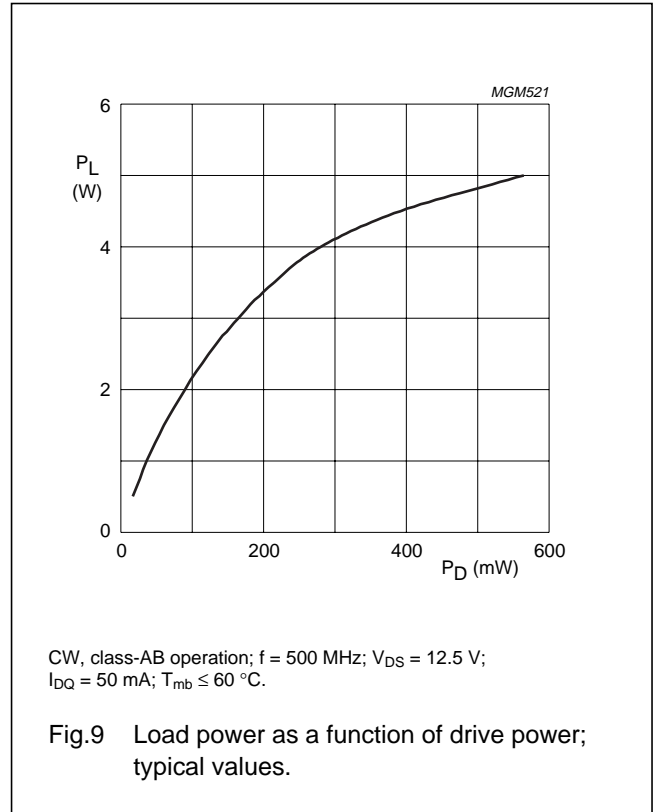
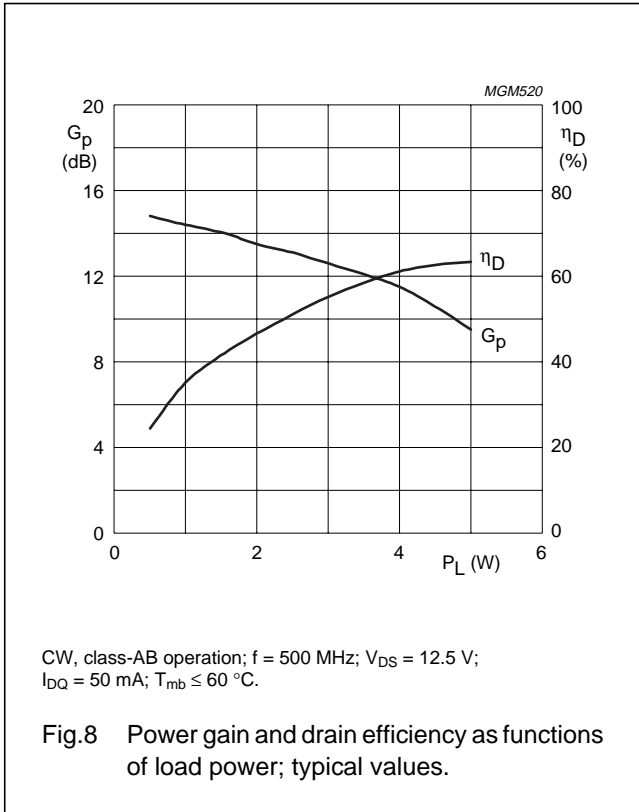
MODE OF OPERATION	f (MHz)	V_{DS} (V)	I_{DQ} (A)	P_L (W)	G_p (dB)	η_D (%)
CW, class-AB	500	12.5	50	4	≥ 10 typ. 11.5	≥ 50 typ. 55

Ruggedness in class-AB operation

The BLF404 is capable of withstanding a load mismatch corresponding to $V_{SWR} = 10 : 1$ through all phases under the following conditions: $f = 500$ MHz; $V_{DS} = 12.5$ V; $P_L = 4$ W; $T_{mb} \leq 60$ °C.

UHF power MOS transistor

BLF404



UHF power MOS transistor

BLF404

List of components; see Figs 10 and 11.

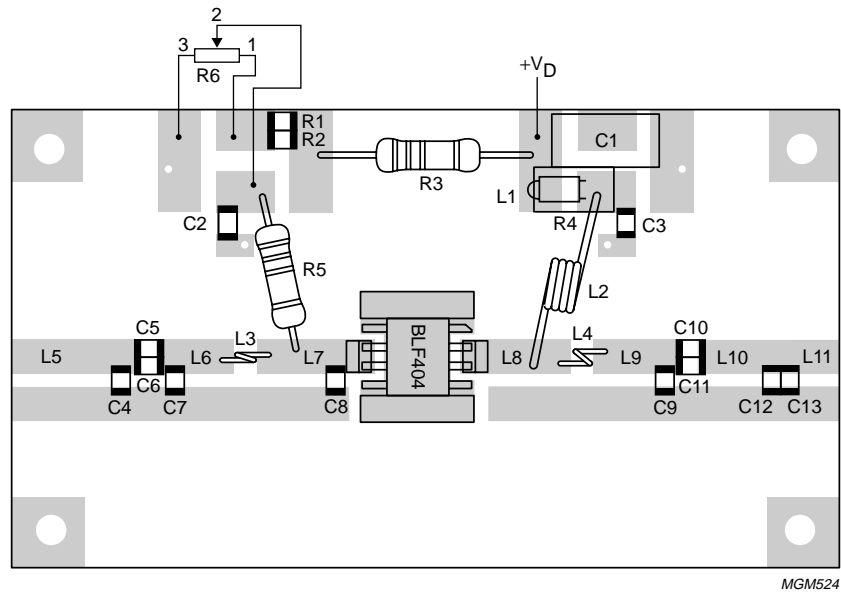
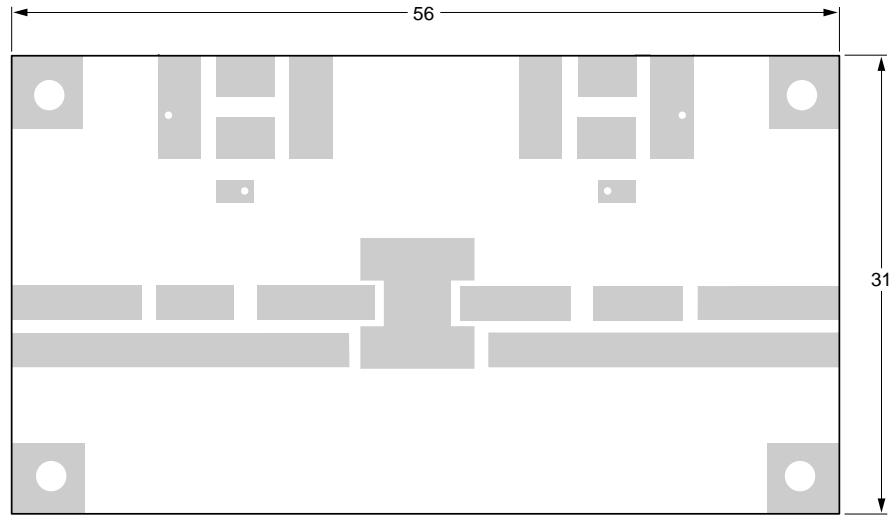
COMPONENT	DESCRIPTION	VALUE	DIMENSIONS	CATALOGUE NO.
C1	electrolytic capacitor	4.7 μ F, 10 V		
C2, C3	multilayer ceramic chip capacitor	47 nF		
C4	multilayer ceramic chip capacitor; note 1	18 pF		
C5, C10	multilayer ceramic chip capacitor; note 1	180 pF		
C6, C11	multilayer ceramic chip capacitor; note 1	270 pF		
C7	multilayer ceramic chip capacitor; note 1	22 pF		
C8	multilayer ceramic chip capacitor; note 1	8.2 pF		
C9	multilayer ceramic chip capacitor; note 1	2.7 pF		
C12	multilayer ceramic chip capacitor; note 1	1.2 pF		
C13	multilayer ceramic chip capacitor; note 1	12 pF		
L1	2 turns 1 mm enamelled copper wire on a grade 4B1 Ferroxcube core		ext. dia. = 4.2 mm int. dia. = 2 mm length = 6 mm	
L2	3 turns 1 mm enamelled copper wire		int. dia. = 4.6 mm leads = 2 x 5 mm	
L3	bifilar coil		lead dia. = 0.8 mm	
L4	bifilar coil		lead dia. = 1 mm	
L5	stripline; note 2	50 Ω	8.8 x 2.38 mm	
L6	stripline; note 2	50 Ω	5.8 x 2.38 mm	
L7	stripline; note 2	50 Ω	6.8 x 2.38 mm	
L8	stripline; note 2	50 Ω	3.76 x 2.38 mm	
L9	stripline; note 2	50 Ω	5.8 x 2.38 mm	
L10	stripline; note 2	50 Ω	4.48 x 2.38 mm	
L11	stripline; note 2	50 Ω	3.13 x 2.38 mm	
R1, R2	SMD resistor	3.9 k Ω		
R3	metal film resistor	1 k Ω , 0.25 W		
R4	metal film resistor	22 Ω , 0.25 W		
R5	metal film resistor	10 k Ω , 0.25 W		
R6	potentiometer	10 k Ω		

Notes

- American Technical Ceramics type 100A or capacitor of same quality.
- The striplines are on a double copper-clad printed-circuit board, with DUROID dielectric ($\epsilon_r = 2.2$); thickness 0.79 mm, thickness of the copper sheet 2 x 35 μ m.

UHF power MOS transistor

BLF404



MGM524

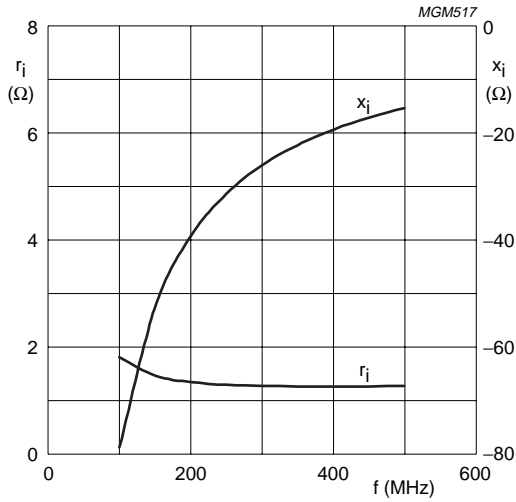
Dimensions in mm.

The components are situated on one side of the copper-clad printed-circuit board, the other side is unetched and serves as a ground plane. Earth connections from the component side to the ground plane are made by through metallization.

Fig.11 Component layout for 500 MHz class-AB test circuit.

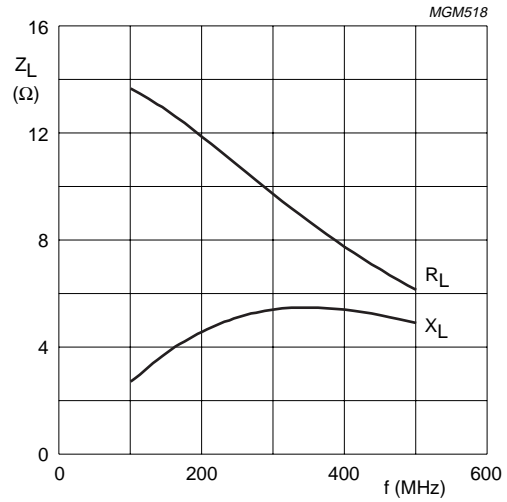
UHF power MOS transistor

BLF404



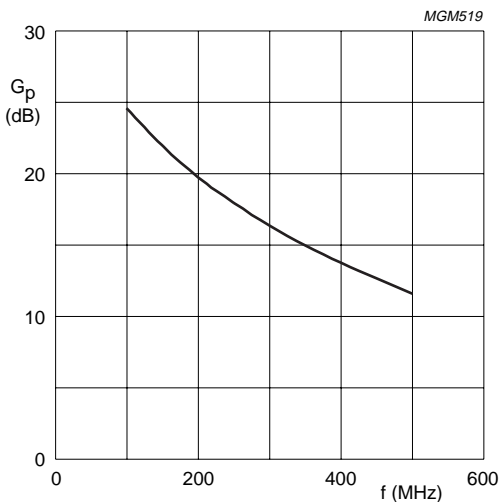
CW, class-AB operation; $V_{DS} = 12.5\text{ V}$; $I_D = 50\text{ mA}$; $P_L = 4\text{ W}$; $T_{mb} \leq 60\text{ }^\circ\text{C}$.

Fig.12 Input impedance as a function of frequency (series components); typical values.



CW, class-AB operation; $V_{DS} = 12.5\text{ V}$; $I_D = 50\text{ mA}$; $P_L = 4\text{ W}$; $T_{mb} \leq 60\text{ }^\circ\text{C}$.

Fig.13 Load impedance as a function of frequency (series components); typical values.



CW, class-AB operation; $V_{DS} = 12.5\text{ V}$; $I_{DQ} = 50\text{ mA}$; $P_L = 4\text{ W}$; $T_{mb} \leq 60\text{ }^\circ\text{C}$.

Fig.14 Power gain as a function of frequency (series components); typical values.

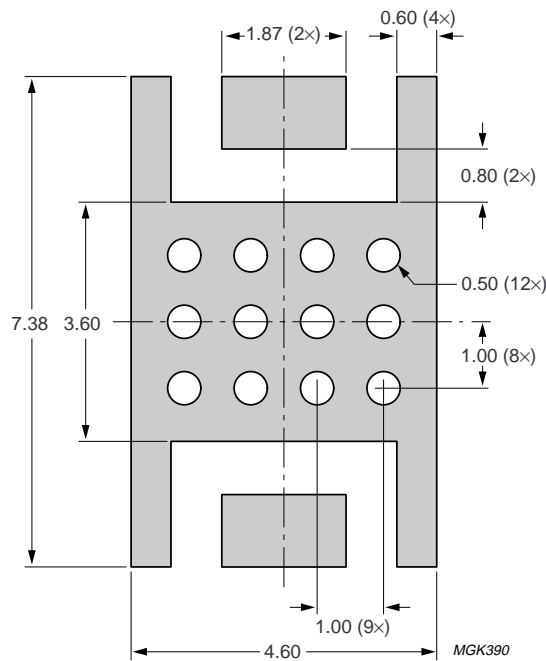
UHF power MOS transistor

BLF404

MOUNTING RECOMMENDATIONS

Both the metallized ground plate and the device leads contribute to the heat flow. It is recommended that the transistor be mounted on a grounded metallized area of the printed-circuit board. This area should be of maximum 0.8 mm thickness and include at least 12 x 0.5 diameter through metallized holes filled with solder.

A thermal resistance $R_{th(mb-h)}$ of 5 K/W can be achieved if heatsink compound is applied when the transistor is mounted on the printed-circuit board.



Dimensions in mm.

Fig.15 Reflow soldering footprint for SOT409A.

UHF power MOS transistor

BLF404

BLF404 scattering parameters $V_{DS} = 12.5\text{ V}$; $I_D = 50\text{ mA}$; note 1.

f (MHz)	S ₁₁		S ₂₁		S ₁₂		S ₂₂	
	S ₁₁	∠Φ	S ₂₁	∠Φ	S ₁₂	∠Φ	S ₂₂	∠Φ
5	1.00	-5.2	12.97	176.0	0.01	86.0	0.96	-6.0
10	0.99	-10.1	12.89	171.9	0.02	82.2	0.96	-12.0
20	0.98	-20.6	12.61	164.1	0.03	74.8	0.95	-23.5
30	0.96	-30.4	12.18	156.6	0.05	67.6	0.93	-34.7
40	0.93	-39.6	11.62	149.6	0.06	60.9	0.91	-45.1
50	0.89	-48.0	11.00	143.2	0.07	54.8	0.89	-54.7
60	0.86	-55.8	10.37	137.4	0.08	49.4	0.87	-63.5
70	0.83	-62.9	9.74	132.2	0.09	44.4	0.85	-71.4
80	0.80	-69.4	9.15	127.5	0.10	40.1	0.83	-78.5
90	0.78	-75.3	8.60	123.2	0.10	36.2	0.82	-84.8
100	0.75	-80.7	8.08	119.3	0.10	32.7	0.80	-90.5
125	0.71	-92.2	6.96	110.7	0.11	25.1	0.77	-102.6
150	0.68	-101.4	6.03	103.9	0.12	19.1	0.76	-111.9
175	0.66	-108.9	5.30	98.3	0.12	14.4	0.74	-119.2
200	0.64	-115.2	4.73	93.2	0.12	10.2	0.74	-125.1
250	0.63	-124.9	3.81	84.5	0.12	3.5	0.73	-134.1
300	0.64	-132.5	3.19	77.4	0.12	-1.8	0.74	-140.5
350	0.64	-138.6	2.70	71.2	0.11	-6.1	0.74	-145.3
400	0.66	-143.8	2.34	65.7	0.11	-9.7	0.75	-149.1
450	0.67	-148.4	2.03	60.5	0.10	-12.5	0.76	-152.4
500	0.69	-152.6	1.80	56.0	0.09	-15.1	0.78	-155.2
600	0.72	-160.2	1.44	47.7	0.08	-18.2	0.80	-159.9
700	0.75	-167.1	1.18	40.4	0.07	-18.6	0.82	-163.9
800	0.78	-173.6	0.99	34.4	0.05	-15.0	0.84	-167.5
900	0.81	-179.8	0.84	29.2	0.04	-6.0	0.86	-170.7
1000	0.83	174.3	0.73	25.1	0.04	9.9	0.88	-173.6

Note

- For more extensive s-parameters see internet:
<http://www.semiconductors.philips.com/markets/communications/wirelesscommunications/broadcast>

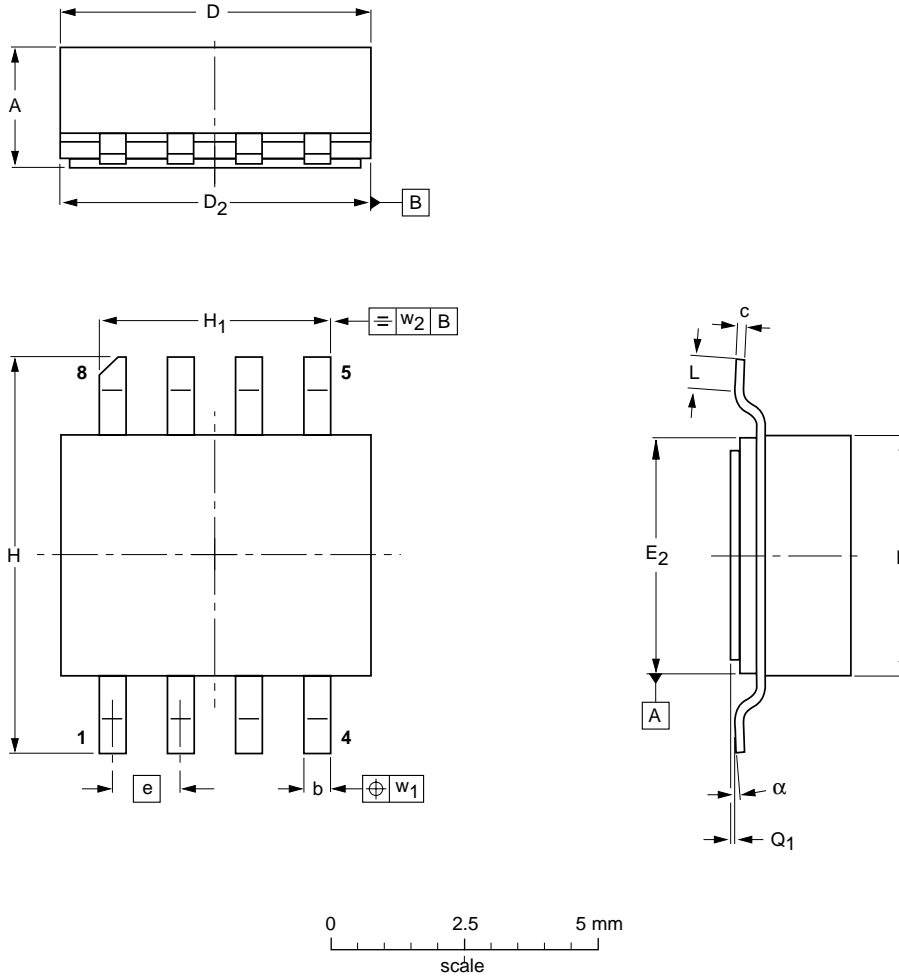
UHF power MOS transistor

BLF404

PACKAGE OUTLINE

Ceramic surface mounted package; 8 leads

SOT409A



DIMENSIONS (millimetre dimensions are derived from the original inch dimensions)

UNIT	A	b	c	D	D ₂	E	E ₂	e	H	H ₁	L	Q ₁	w ₁	w ₂	α
mm	2.36 2.06	0.58 0.43	0.23 0.18	5.94 5.03	5.16 5.00	4.93 4.01	4.14 3.99	1.27	7.47 7.26	4.39 4.24	1.02 0.51	0.10 0.00	0.25	0.25	7° 0°
inches	0.093 0.081	0.023 0.017	0.009 0.007	0.234 0.198	0.203 0.197	0.194 0.158	0.163 0.157	0.050	0.294 0.286	0.173 0.167	0.040 0.020	0.004 0.000	0.010	0.010	7° 0°

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT409A						98-01-27

UHF power MOS transistor

BLF404

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Printed in The Netherlands

613524/04/pp15

Date of release: 2003 Sep 26

Document order number: 9397 750 11603

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